

iscN-Channel MOSFET Transistor

TK5A65D

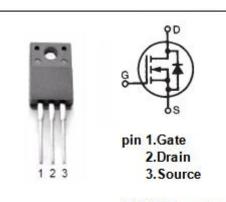
| FEATURES |
|------------------------------|
|------------------------------|

- Low drain-source on-resistance: $R_{DS}(ON) = 1.43\Omega$ (MAX)
- Enhancement mode:
 - Vth = 2 to 4V (VDS = 10 V, ID=1.0mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)



J -----

0.75

3.10

3.70

0.50

13.4 1.10

5.00

2.70

2.20

2.65

6.40

mm MIN

14.95 15.05 10.00 10.10 4.40

MAX

4.60

0.90

3.30

3.90

0.70 13.6

1.30 5.20

2.90

2.40

6.60

2.90

TO-220F package

| | | | | → B → → | | |
|------------------|--|---------|------|---------|---|--|
| SYMBOL | PARAMETER | VALUE | UNIT | 0 _ 0 Q | | |
| VDSS | Drain-Source Voltage | 650 | V | FOO | | |
| V _{GS} | Gate-Source Voltage | ±30 | v | L | T | |
| ١D | Drain Current-Continuous | 5 | А | | ĸ | |
| I _{DM} | Drain Current-Single Pulsed | 20 | A | D N | ł | |
| P _D | Total Dissipation @T _c =25℃ | 40 | w | DI | 1 | |
| Tj | Max. Operating Junction Temperature | 150 | °C | |) | |
| T _{stg} | Storage Temperature | -55~150 | °C | | | |
| • THERM | IAL CHARACTERISTICS | | | | ī | |
| SYMBOL | PARAMETER | МАХ | UNIT | R | | |
| Rth(ch-c) | Channel-to-case thermal resistance | 3.125 | °C/W | | | |

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ELECTRICAL CHARACTERISTICS

$T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | МАХ | UNIT |
|---------------------|--------------------------------|--|-----|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 10mA | 650 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{DS} = 10V; I _D =1.0mA | 2 | | 4 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D =2.5A | | | 1.43 | Ω |
| lgss | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} = 0V | | | ±1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =650V; V _{GS} = 0V | | | 10 | μA |
| V _{SDF} | Diode forward voltage | I _{DR} =5A, V _{GS} = 0 V | | | 1.7 | V |



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